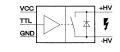
## **FAST HIGH VOLTAGE TRANSISTOR SWITCHES**

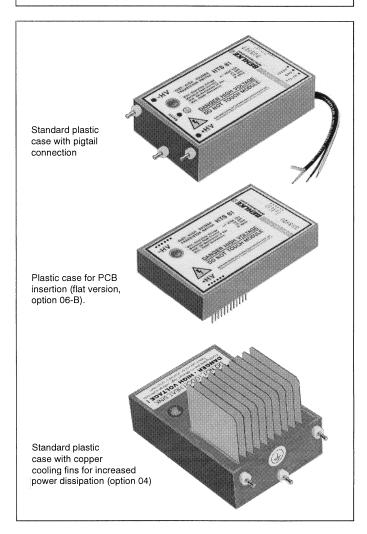
These MOSFET switches are designed for general high voltage switching applications such as pockels cell drivers, deflection and acceleration grid drivers, piezo drivers, MCP/SEV pulsers and converters. The switching modules incorporate all features of the well known HTS switch family: Easy handling, high reliability, low jitter and precise switching. In contrast to conventional high voltage switches like spark gaps, electron tubes, gas discharge tubes and mechanical switches, HTS transistor switches show very stable switching characteristics independent of temperature and age. The mean time between failures (MTBF) is by several orders of magnitude higher than that of the classical HV switches. The switching modules are controlled by an interference-proof driver circuit which provides signal conditioning, auxiliary voltage monitoring, frequency limitation and temperature protection. In case of false operating conditions the switches are immediately turned-off and a fault signal is generated (not available for "pigtail" devices). The switches are turned-on by a positive going signal of 2 to 10 volts amplitude. The on-time may be varied between 100 ns and infinity. A short recovery time of 300 ns allows burst frequencies up to 3.3 MHz. Due to the galvanic isolation of more than 10 kV the switches may simply be operated also in high-side circuits. Three housing options are available to meet individual electrical and constructive requirements. The plastic case is the cost-effective standard package in low frequency, pulsed power applications with a low continuous power dissipation. The standard housing has soldering terminals and "pigtails" for connection. It is also available as a printed circuit board version with soldering pins at bottom (option 06). To increase the Maximum Power Dissipation  $\boldsymbol{P}_{\text{\tiny d(max)}}$  the plastic modules can additionally be fitted with non-isolated cooling fins (option 04), which improve the Pd(max) value by approximately the factor 5. A metal case for a continuous power dissipation of up to 400 Watt is also available (option 05, cf. data sheet "High Power Metal Case"). For detailed design recommendations please refer to the general instructions.

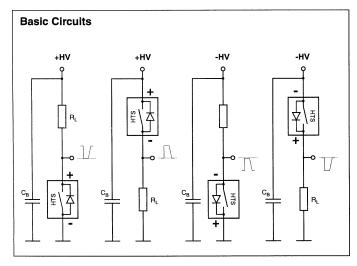
HTS 31 HTS 51 HTS 81

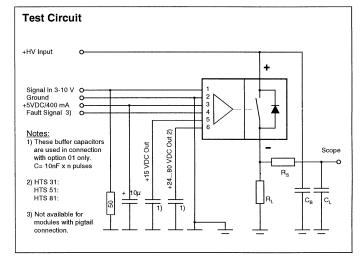
3000 VDC / 30 Amps 5000 VDC / 30 Amps 8000 VDC / 30 Amps

High Frequency Variable On-Time











## **TECHNICAL DATA**

Specification	Symbol	Condition / Comment		HTS 31	HTS 51	HTS 81	Unit
Maximum Operating Voltage	$V_{O(max)}$	I <sub>off</sub> < 10 μADC		3000	5000	8000	VDC
Minimum Operating Voltage	$V_{O(min)} \\$	Increased $t_{r(on)}$ and $t_{r(off)}$ below 0.1x $V_{O(max)}$			0		VDC
Typical Breakdown Voltage	$V_{br}$	I <sub>off</sub> > 1mADC, T <sub>case</sub> = 70 °C		3600	6000	9600	VDC
Galvanic Isolation	Vı	HV part against control, standard			>10000		VDC
Maximum Peak Current	I <sub>P(max)</sub>	T <sub>case</sub> = 25°C	t <sub>p</sub> <10 μs, duty cycle <1%		30		
			t <sub>p</sub> <100µs, duty cycle <1%		24		
			t <sub>p</sub> <1 ms, duty cycle <1%		17		ADC
Maximum Continuous	IL	T <sub>case</sub> = 25°C	Standard plastic case	0.71	0.58	0.45	
Load Current		respectively	Ditto + option 03	0.87	0.71	0.55	
		T <sub>fin</sub> = 25°C	Ditto +cooling fins (opt. 04)	-	-	1.09	
			Metal case B1 (opt. 05)	-	-	2.83	ADC
Static On-Resistance	R <sub>stat</sub>	T <sub>case</sub> = 25°C	0.1 x I <sub>P(max)</sub>	8	12	20	
			@ I <sub>P(max)</sub>	20	30	50	Ω
Maximum Off-State Current	I <sub>off</sub>	0.8 x V <sub>O</sub> , T <sub>case</sub> = 2570°C			5		μADC
Turn-On Delay Time	t <sub>d(on)</sub>	@ I <sub>P(max)</sub>		100		ns	
Typical Turn-On Rise Time	t <sub>r(on)</sub>	0.8 x V <sub>O</sub> ,	0.1 x I <sub>P(max)</sub>		6		
31	.(5.1)	10-90 %	1.0 x I <sub>P(max)</sub>		9		ns
Typical Turn-Off Rise Time	t <sub>r(off)</sub>	0.8xV <sub>0</sub> 0.1x I <sub>1</sub>	P <sub>(max),</sub> resistive load, 10-90%		7		ns
Minimum On-Time	t <sub>on(min)</sub>	Limited by driv	• •		100		ns
Maximum On-Time	t <sub>on(max)</sub>		ossible P <sub>d(max)</sub> limitations		∞		110
Switch Recovery Time	t <sub>rc</sub>				300		ns
Typical Turn-On Jitter	1.	t <sub>rc</sub> = minimum pulse spacing  V <sub>aux</sub> / V <sub>tr</sub> = 5.0 VDC			100		-
• •	t <sub>j(on)</sub>			100	70	40	ps kHz
Max. Switching Frequency	f <sub>(max)</sub>	Please note possible P <sub>d(max)</sub> limitations		100		40	
Maximum Burst Frequency	f <sub>b(max)</sub>	•	for >10 pulses within<20µs	10	3.3	10	MHz
Maximum Continuous Power	$P_{d(max)}$	T <sub>case</sub> = 25°C	Standard plastic case	10	10 15	10 15	
Dissipation		respectively T <sub>fin</sub> = 25°C	Ditto + option 03	15	15	15 60	
		I fin = 25 C	Ditto +cooling fins (opt. 04) Metal case B1 (opt. 05)	_	-	400	Watts
5			1 1 1	-	-		walls
Linear Derating		Above 25 °C	Standard plastic case	0.22	0.22	0.22	
			Ditto + option 03	0.33	0.33	0.33	
			Ditto + cooling fins (opt. 04)	-	-	1.33	10///2
Tanasantus Danas	-	Distriction	Metal case B1 (opt. 05)	-	- 40. 70	6.66	W/K
Temperature Range	To		lastic case, plastic case +cooling fins		-4070		°C
		Metal case B1 (option 05)		110	-3085		°C
Natural Capacitance	C <sub>N</sub>	Capacitance between switch poles at V <sub>O(max)</sub>		110	75	45	pF
Coupling Capacitance	C <sub>C</sub>	HV side agains			16		pF
Diode Reverse Recovery Time	t <sub>rrc</sub>	$I_F=0.1xI_{P(max)}$	MOSFET parasitic diode	_	500		ns
Diode Forward Voltage Drop	V <sub>F</sub>	$I_F=0.1xI_{P(max)}$	MOSFET parasitic diode	6	9	15	VDC
Auxiliary Supply Voltage	V <sub>aux</sub>	Stabilized to ±	5%		5.0		VDC
Auxiliary Supply Current	l <sub>aux</sub>	@ f <sub>max</sub>			400		mADC
Control Signal	$V_{tr}$	> 3VDC recommended		2-10		VDC	
Fault Signal Output		TTL compatible, short circuit proof, L=Fault		H= 4 V, L= 0.5 V		VDC	
Dimensions	LxBxH	Standard plastic case		89 x 64 x 27			
		Flat plastic case (opt. 06-B)		89 x 64 x 19			
		Plastic case + cooling fins (opt. 04)  Metal case B1 (opt. 05)  Standard plastic case		89 x 64 x 60			_
	<del> </del>			180 x 100 x 53.5			mm <sup>3</sup>
Weight				250			
			se (opt. 06-B)		190		
			cooling fins (opt. 04)		350		
		Metal case B1	(opt. 05)		2500		g

## **Ordering Informations**

HTS 31	Transistor switch, 3000 VDC, 30 Amps.	Option 04	Cooling fins, non-isolated
HTS 51	Transistor switch, 5000 VDC, 30 Amps.	Option 05	Metal case B1, potential-free (cf. separate data sheet)
HTS 81	Transistor switch, 8000 VDC, 30 Amps.	Option 06	Soldering pins for printed boards, module height 27 mm
Option 01	High frequency burst	Option 06-B	Ditto, module height 19 mm (options 02,03, 04 excluded)
Option 02	Flame retardend casting resin UL94-VO	Option 08	30 kV instead of 10 kV isolation, module size on request
Option 03	Increased thermal conductivity	Option 08-B	80 kV instead of 10 kV isolation, module size on request

All data and specifications subject to change without notice. Custom designed devices on request.